



PNP/NPN Epitaxial Planar Silicon Transistors

2SA1826/2SC4730

100V/3A Switching Applications

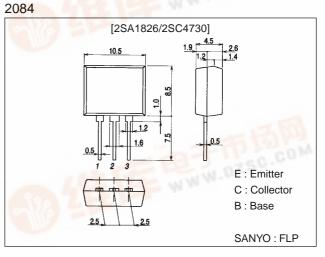
Applications

• Relay drivers, high-speed inverters, converters, and other general high-current switching applications.

Features

- · Low collector-to-emitter saturation voltage.
- · High Gain-Bandwidth Product.
- · Excellent linearity of DC Current Gain.
- · Fast switching speed.

Package Dimensions



():2SA1826

Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		(–)120	V
Collector-to-Emitter Voltage	VCEO		(–)100	V
Emitter-to-Base Voltage	V _{EBO}		(-)6	V
Collector Current	IC		(-)3	Α
Collector Current (Pulse)	I _{CP}	1 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2 2	(–)6	Α
Base Current	IB	A 44121	()0.6	A
Collector Dissipation	PC		1.5	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions		Ratings		
Falameter				typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)100V, I _E =0			(–)1	μΑ
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0			(-)1	μA
DC Current Gain	h _{FE} 1	V _{CE} =(-)5V, I _C =(-)500mA	100*		400*	Acres 1
	h _{FE2}	V _{CE} =(-)5V, I _C =(-)2A	40		50-1	
Gain-Bandwidth Product	fT	V _{CE} =(-)10V, I _C =(-)500mA	in M	(130)		MHz
				180		MHz

 \ast : The 2SA1826/2SC4730 are classified by 500mA h_{FE} as follows :

100 R 200 140 S 280 200 T 400

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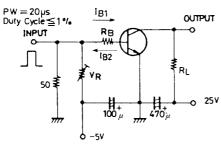
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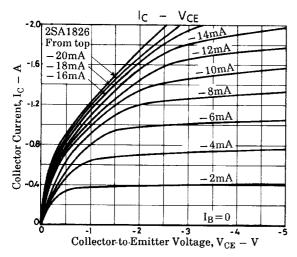
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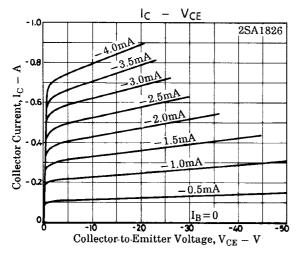
Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Output Capacitance	Cob	V _{CB} =(-)10V, f=1MHz		(40)25		pF
Collector-to-Emitter Saturation Voltage	VCE(sat)	I _C =(-)1.5A, I _B =(-)0.15A		(-200)	(500)	mV
				150	400	mV
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =(-)1.5A, I _B =(-)0.15A		(–)0.9	(–)1.2	mV
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)10µA, I _E =0	(–)120			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(−)1mA, R _{BE} =∞	()100			V
Emitter-to-Base Breakdown Voltage	V _{(BR)EBO}	I _E =(-)10μA, I _C =0	(-)6			V
Turn-ON Time	t _{on}	See specified Test Circuit		100		ns
Storage Time	t _{stg}	See specified Test CIrcuit		(800)		ns
				900		ns
Fall Time	t _f	See specified Test Circuit		50		ns

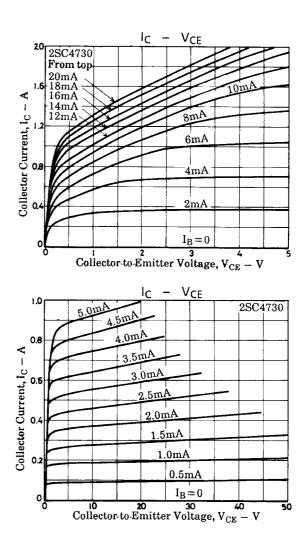
Switching Time Test Circuit



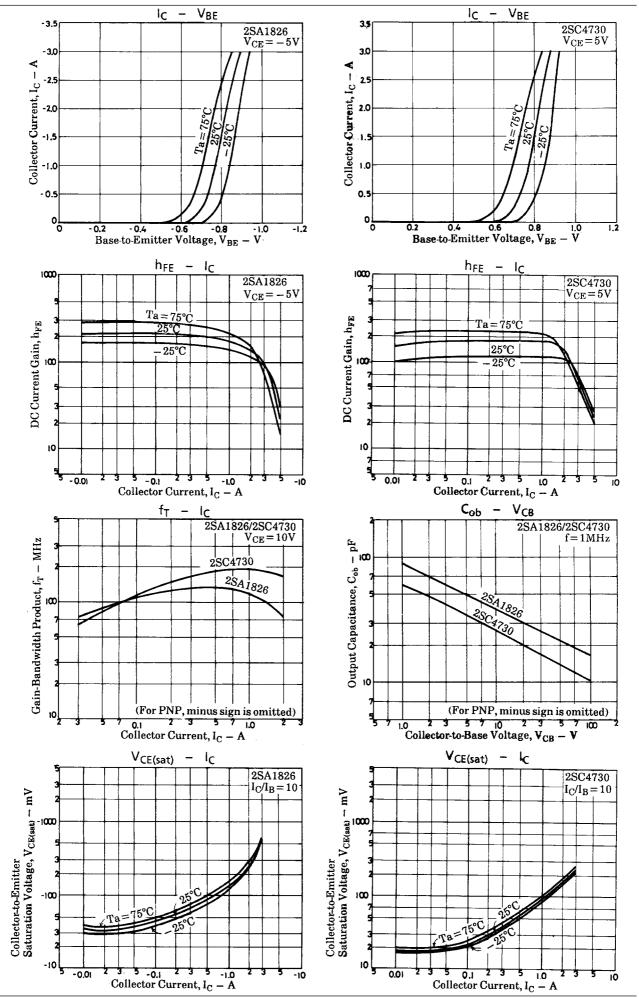
$$\begin{split} I_C = 10I_B 1 = -10I_B 2 = 1.5A \\ \text{(For PNP, the polarity is reversed).} \\ \text{Unit (resistance : } \Omega, \text{ capacitance : F)} \end{split}$$



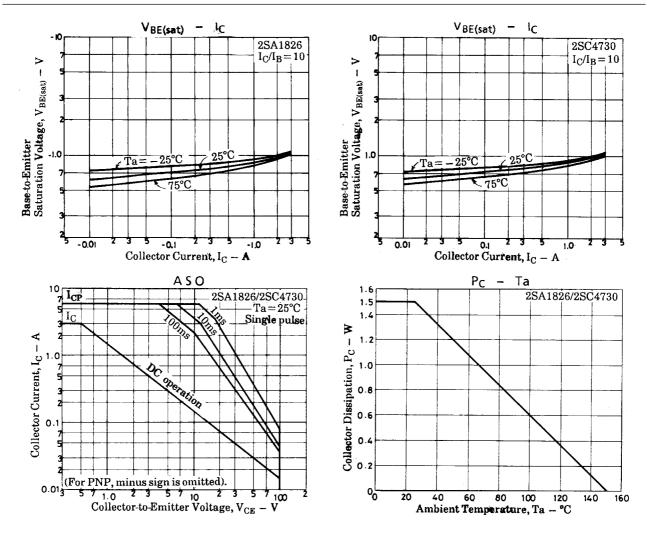




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